Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100% solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM

3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	11.4	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 7.9 \text{ A}; T_j = 25 \text{ °C}$		-	12	16	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain	7 7	
3	G	gate		G T
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMPB12UNE	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB12UNE	2Y

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$	[1]	-	11.4	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	7.9	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	32	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	470	mW
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	1.56	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode	1	1	1	1	
I _S	source current	T _{amb} = 25 °C	[1]	-	1.5	Α

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

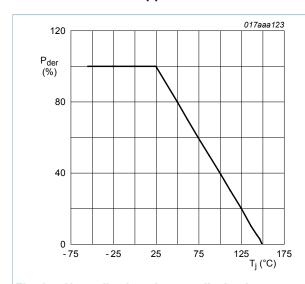


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

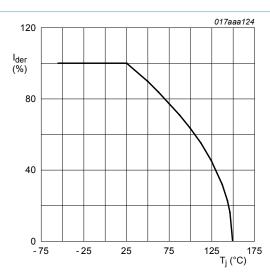


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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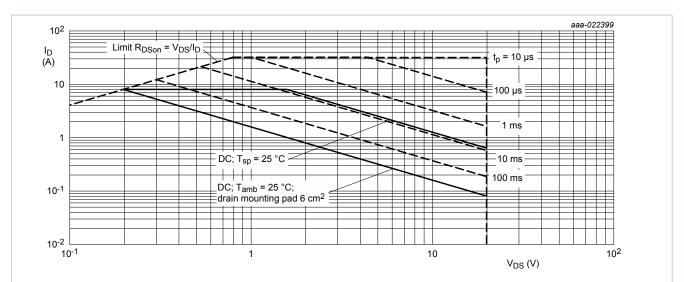


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

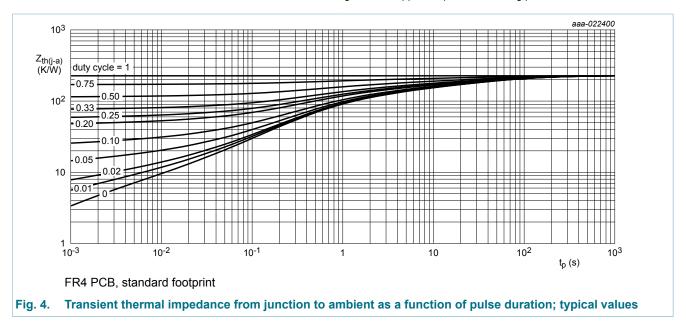
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9. Thermal characteristics

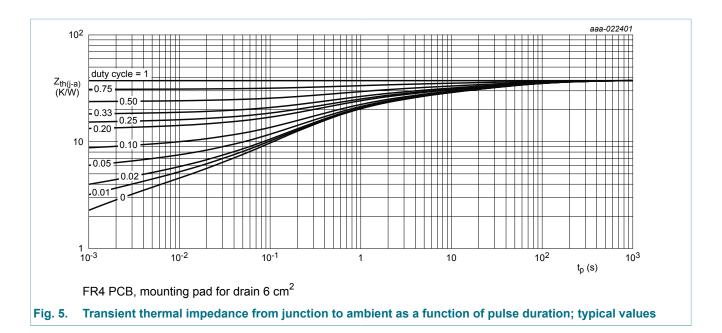
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	230	265	K/W
	from junction to ambient		[2]	-	70	80	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	34	39	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μΑ
I _{GSS} gate leakage current	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 7.9 A; T_j = 25 °C	-	12	16	mΩ
		V _{GS} = 4.5 V; I _D = 7.9 A; T _j = 150 °C	-	19	25	mΩ
		V_{GS} = 2.5 V; I_D = 7.1 A; T_j = 25 °C	-	15	20	mΩ
		V _{GS} = 1.8 V; I _D = 1.9 A; T _j = 25 °C	-	20	29	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 7.9 A; T_j = 25 °C	-	18	-	S
R _G	gate resistance	f = 1 MHz	-	1.8	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 6 A; V_{GS} = 4.5 V;	-	10.9	17	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.3	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	1220	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	124	-	pF
C _{rss}	reverse transfer capacitance		-	102	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; I _D = 6 A; V _{GS} = 4.5 V;	-	10	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	32	-	ns
t _f	fall time		-	34	-	ns
Source-drai	in diode		'	,		
V_{SD}	source-drain voltage	I _S = 1.5 A; V _{GS} = 0 V; T _j = 25 °C	-	0.7	1.2	V
	The state of the s	1				

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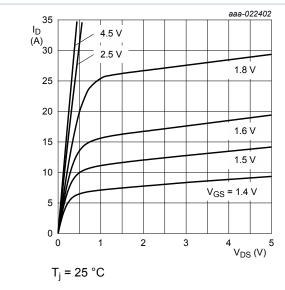


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

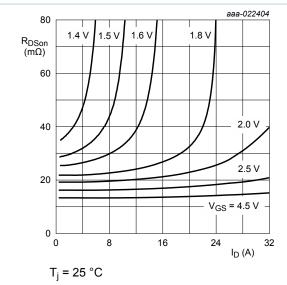


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

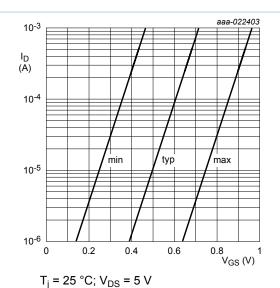


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

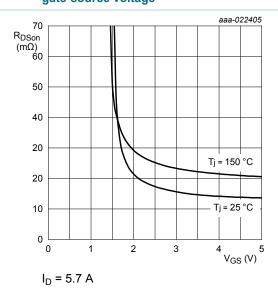


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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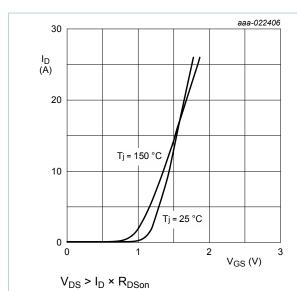


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

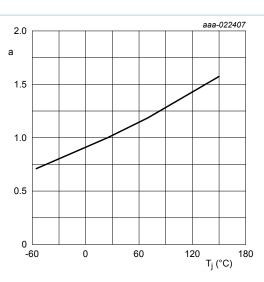


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

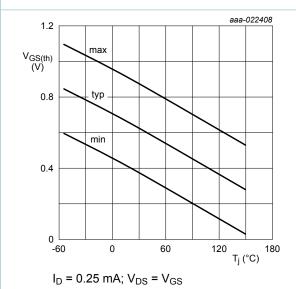
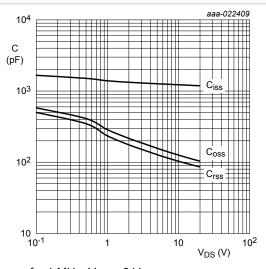


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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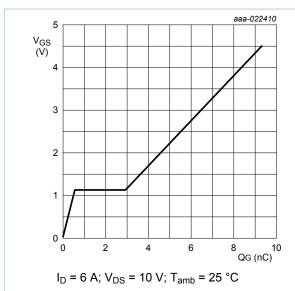


Fig. 15. Gate charge waveform definitions

Q_{GS1}

Q_{GS2}

Q_{G(tot)}-

003aaa508

 Q_{GS}

V_{DS} __

 $V_{\text{GS}(\text{pl})}$

 $\begin{matrix} V_{GS(th)} \\ V_{GS} \end{matrix}$



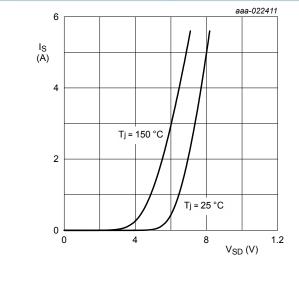
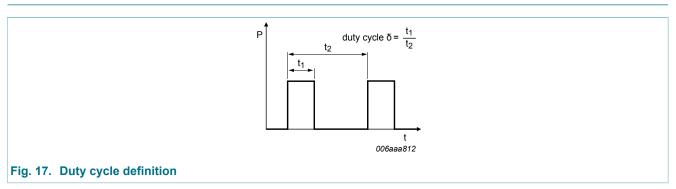


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

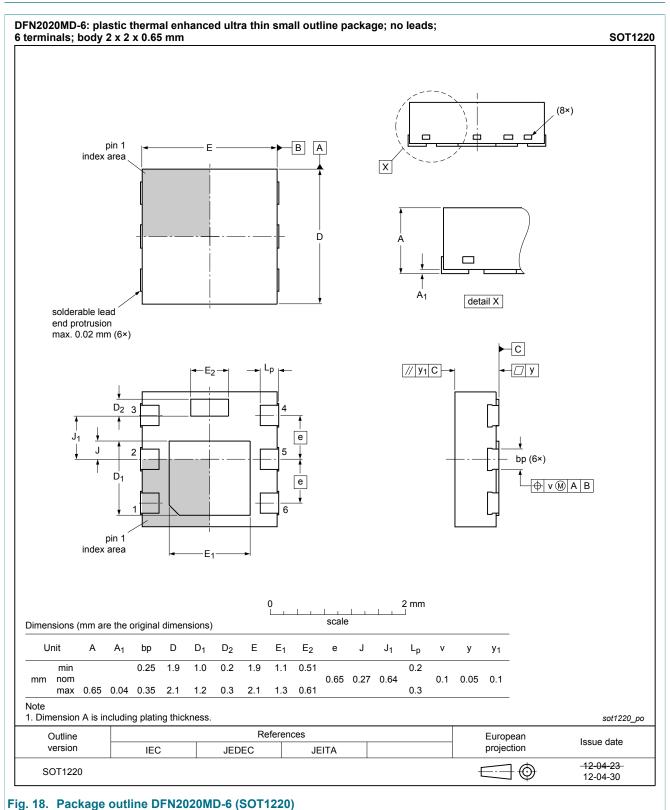
 $V_{GS} = 0 V$



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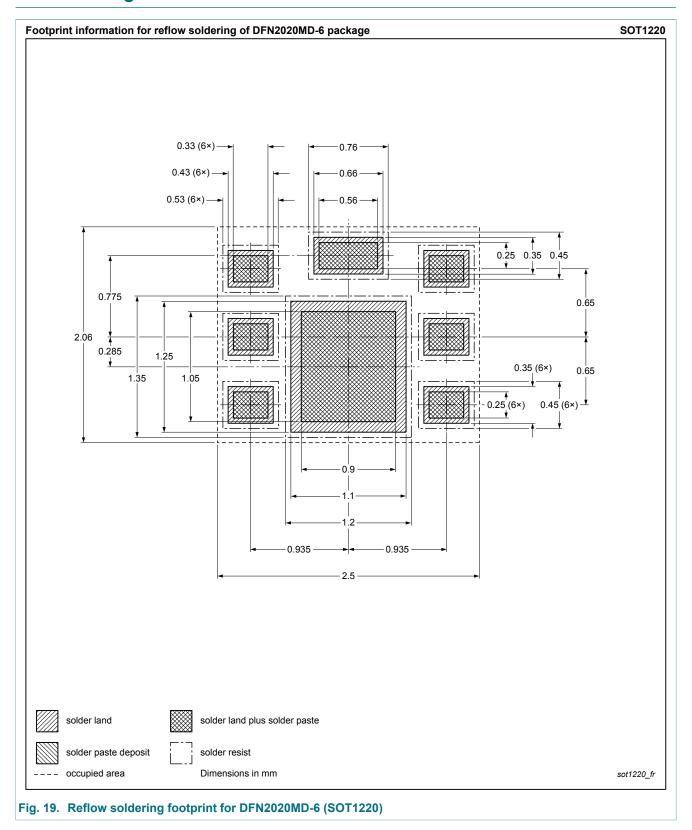
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB12UNE v.1	20160412	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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